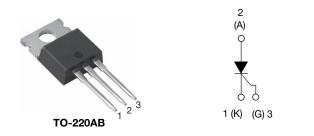


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Thyristor High Voltage, Phase Control SCR, 25 A



PRODUCT SUMMARY		
Package	TO-220AB	
Diode variation	Single SCR	
I _{T(AV)}	16 A	
V _{DRM} /V _{RRM}	800 V, 1200 V	
V _{TM}	1.25 V	
I _{GT}	45 mA	
TJ	- 40 °C to 125 °C	

FEATURES

- Designed and qualified according to JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS				
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS	
Capacitive input filter $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, common heatsink of 1 °C/W	18	22	А	

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	16	۸		
I _{RMS}		25	A		
V _{RRM} /V _{DRM}		800/1200	V		
I _{TSM}		320	А		
V _T	16 A, T _J = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		- 40 to 125	°C		

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA		
VS-25TTS08PbF, VS-25TTS08-M3	800	800	10		
VS-25TTS12PbF, VS-25TTS12-M3	1200	1200	10		

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VS-25TTS..PbF Series, VS-25TTS..-M3 Series

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ABSOLUTE MAXIMUM RATINGS	5						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES		
PARAMETER			NDITION5	TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 93 ^{\circ}{\rm C}$, 180° conduc	ction half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	25	А	
Maximum peak, one-cycle,	1	10 ms sine pulse, rated	V _{RRM} applied	2	70		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no vol	tage reapplied	3	20	1	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated	V _{RRM} applied	365		A ² s	
viaximum i tior rusing	1-1	10 ms sine pulse, no voltage reapplied			15	A-s	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10 ms, no volta	ige reapplied	51	52	A²√s	
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.	25	V	
On-state slope resistance	r _t	T 405.00		12	2.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.0		V	
	1 /1	T _J = 25 °C		0	.5		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	1	0	1	
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		-	150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		20	00]	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 °C, $V_{DRM} = R_g - k = Open$		50	00	V/µs	
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0	\neg	
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V	
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V Deted value	0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T - 125 °C	4	μs
Typical turn-off time	tq	T _J = 125 °C	110	

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.1	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque –	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf ⋅ in)
Marking daviaa			Case style TO 220AP	25TTS08	
Marking device			Case style TO-220AB	25TTS12	

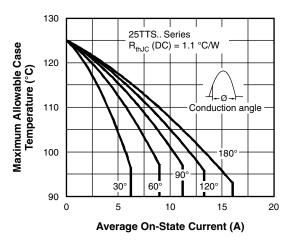


Fig. 1 - Current Rating Characteristics

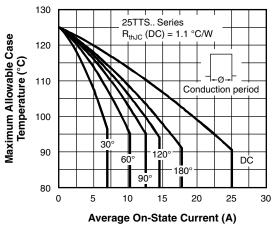


Fig. 2 - Current Rating Characteristics

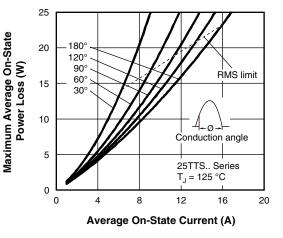


Fig. 3 - On-State Power Loss Characteristics

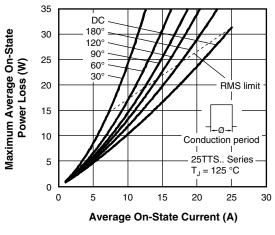


Fig. 4 - On-State Power Loss Characteristics

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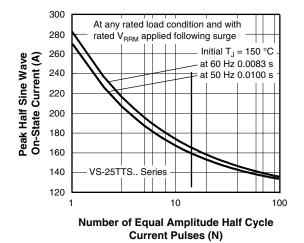


Fig. 5 - Maximum Non-Repetitive Surge Current

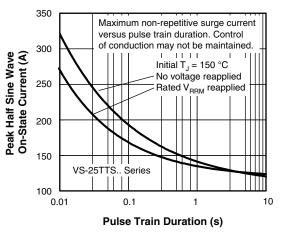


Fig. 6 - Maximum Non-Repetitive Surge Current

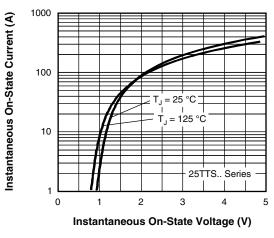


Fig. 7 - On-State Voltage Drop Characteristics

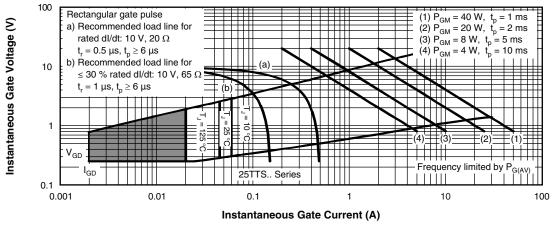


Fig. 8 - Gate Characteristics

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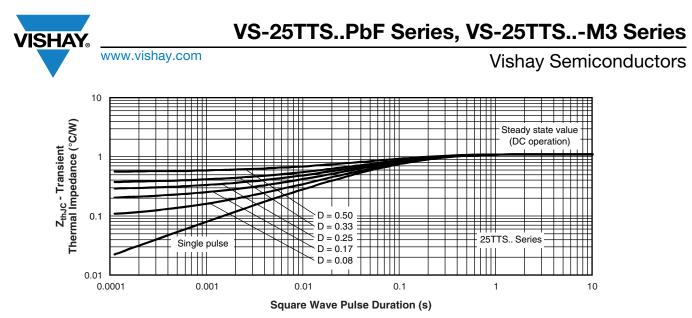


Fig. 9 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	т	т	s	12	PbF	
		(2)	(3)	(4)	(5)	(6)	(7)	
			\bigcirc	4	0	\bigcirc	(\mathbf{r})	
	1 ·	- Visł	nay Sem	niconduc	ctors pro	duct		
	2 -	- Cur	rent rati	ng (25 =	: 25 A)			
	3 -	Circ	uit conf	iguratior	ו:			
		T =	Single t	hyristor				
	4 -	- Pac	kage:					
		T =	TO-220	AB				
	5 -	. Тур	e of silio	con:				
		S =	Standa	rd recov	ery recti	fier		
	6 -	- Volt	age rati	ng —				3 = 800 V = 1200 V
	7	- Envi	ronmen	tal digit:			12	.200 1
		PbF	= Lead	(Pb)-fre	e and R	oHS co	mpliant	
							-	terminations lead (Pb)-fr

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08PbF	50	1000	Antistatic plastic tubes		
VS-25TTS08-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12PbF	50	1000	Antistatic plastic tubes		
VS-25TTS12-M3	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS		
Dimensions		www.vishay.com/doc?95222
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028

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TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NUTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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